Ordering number : ENA1854B

SCH1436

N-Channel Power MOSFET
30V, 1.8A, 180mΩ, Single SCH6

ON Semiconductor®
http://onsemi.com

Features

- ON-resistance $R_{DS}(on)1$=135mΩ(typ.)
- 4V drive
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta=25°C

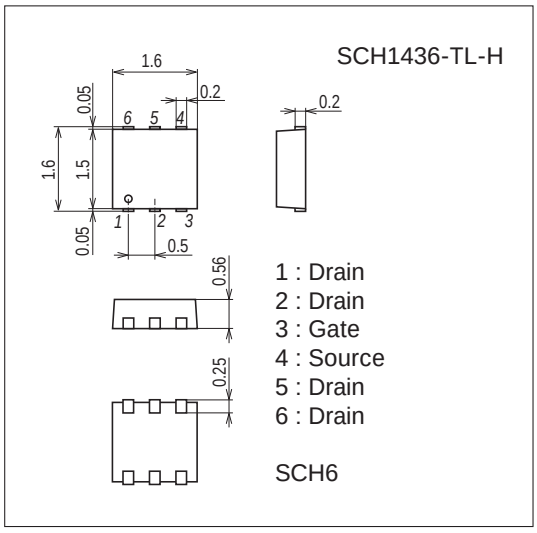
Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	V_{DSS}		30	V
Gate to Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		1.8	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	7.2	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.
* Machine Model

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

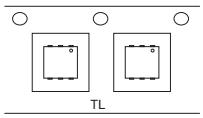
unit : mm (typ)
7028-002



Product & Package Information

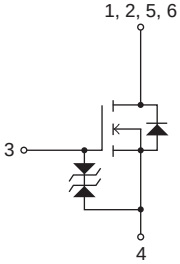
- Package : SCH6
- JEITA, JEDEC : SOT-563
- Minimum Packing Quantity : 5,000 pcs./reel

Packing Type : TL



Marking

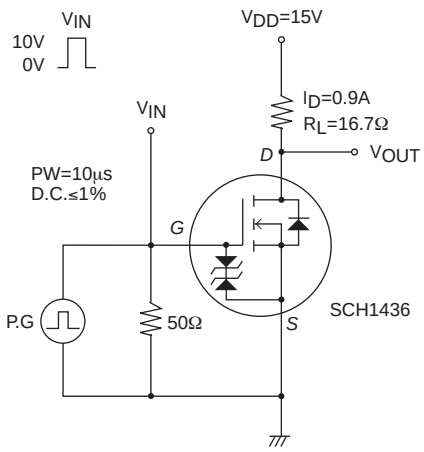
Electrical Connection



Electrical Characteristics at Ta=25°C

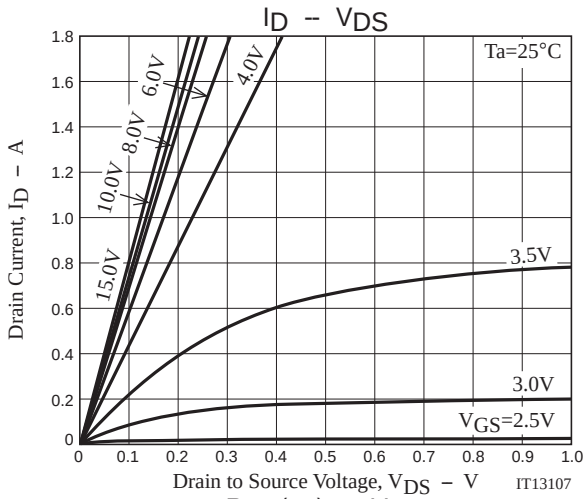
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=10V, I_D=1mA	1.2		2.6	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=0.9A		1.1		S
Static Drain to Source On-State Resistance	$R_{DS}(on)1$	I_D=0.9A, V_{GS}=10V		135	180	mΩ
	$R_{DS}(on)2$	I_D=0.5A, V_{GS}=4V		230	330	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		88		pF
Output Capacitance	Coss			19		pF
Reverse Transfer Capacitance	Crss			11		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		3.4		ns
Rise Time	t_r			4.0		ns
Turn-OFF Delay Time	$t_d(off)$			10.4		ns
Fall Time	t_f			4.2		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=1.8A		2.0		nC
Gate to Source Charge	Qgs			0.33		nC
Gate to Drain “Miller” Charge	Qgd			0.29		nC
Diode Forward Voltage	V_{SD}	I_S=1.8A, V_{GS}=0V		0.86	1.2	V

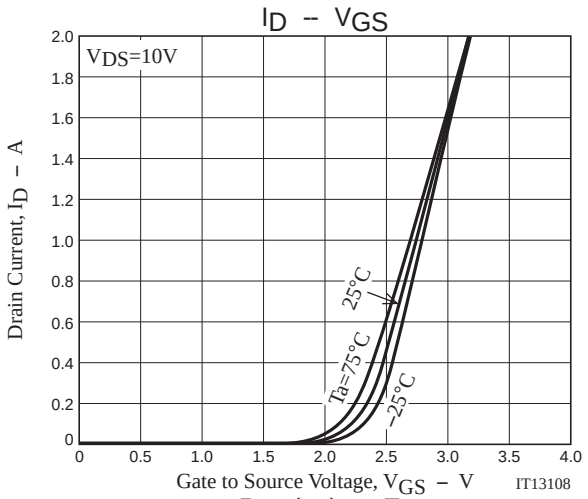
Switching Time Test Circuit

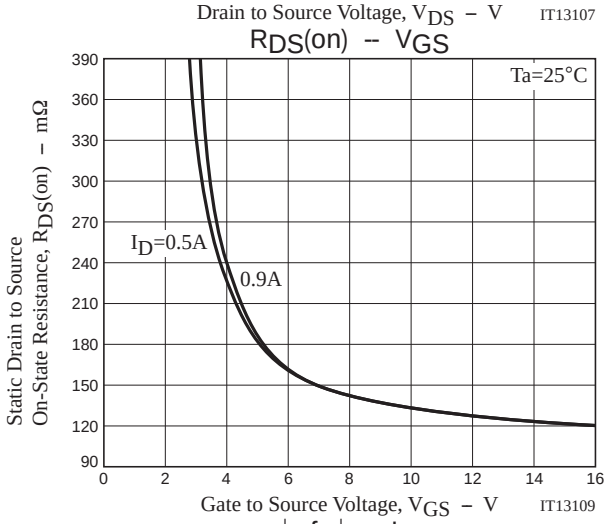


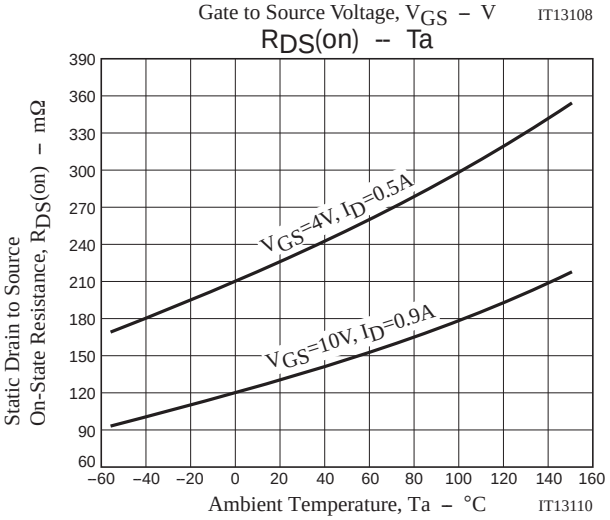
Ordering Information

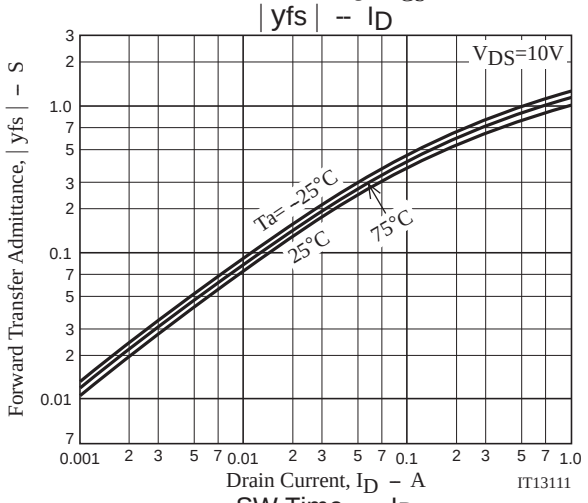
Device	Package	Shipping	memo
SCH1436-TL-H	SCH6	5,000pcs./reel	Pb Free and Halogen Free

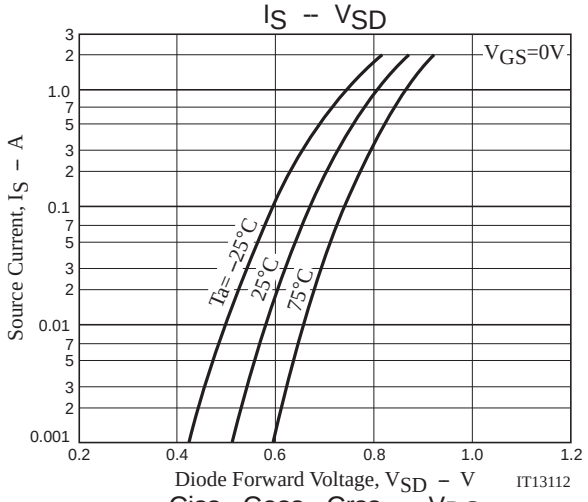

ID -- VDS
Ta=25°C
6.0V
4.0V
8.0V
10.0V
15.0V
3.5V
3.0V
VGS=2.5V
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT13107

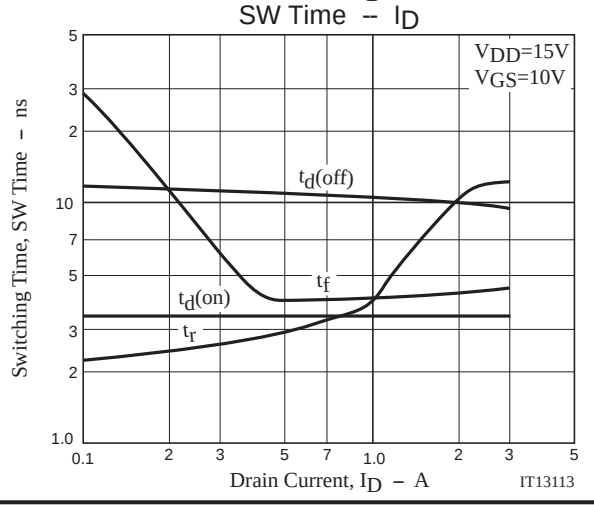

ID -- VGS
VDS=10V
25°C
Ta=75°C
–25°C
Drain Current, ID – A
Gate to Source Voltage, VGS – V
IT13108

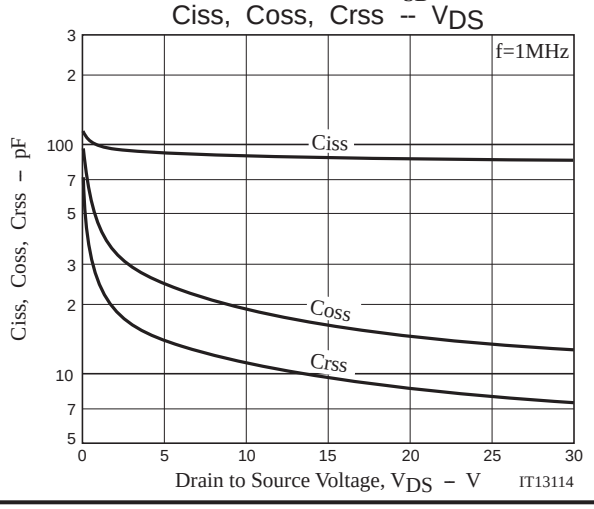

RDS(on) -- VGS
Ta=25°C
ID=0.5A
0.9A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Gate to Source Voltage, VGS – V
IT13109

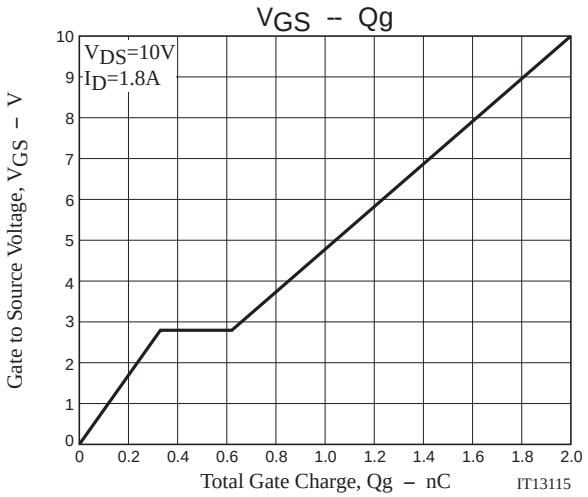

RDS(on) -- Ta
VGS=4V, ID=0.5A
VGS=10V, ID=0.9A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT13110

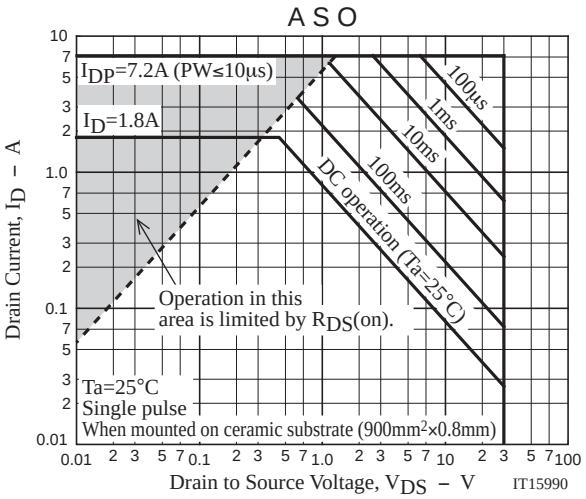

| yfs | -- ID
VDS=10V
Ta= –25°C
25°C
75°C
Forward Transfer Admittance, | yfs | – S
Drain Current, ID – A
IT13111

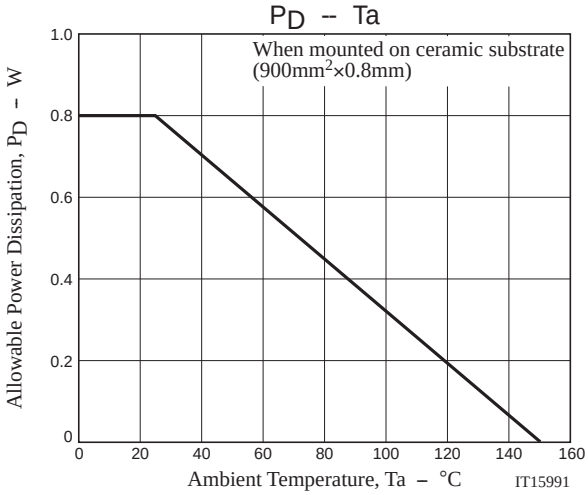

IS -- VSD
VGS=0V
Ta= –25°C
25°C
75°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT13112


SW Time -- ID
VDD=15V
VGS=10V
td(off)
tf
td(on)
tr
Switching Time, SW Time – ns
Drain Current, ID – A
IT13113


Ciss, Coss, Crss -- VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain to Source Voltage, VDS – V
IT13114

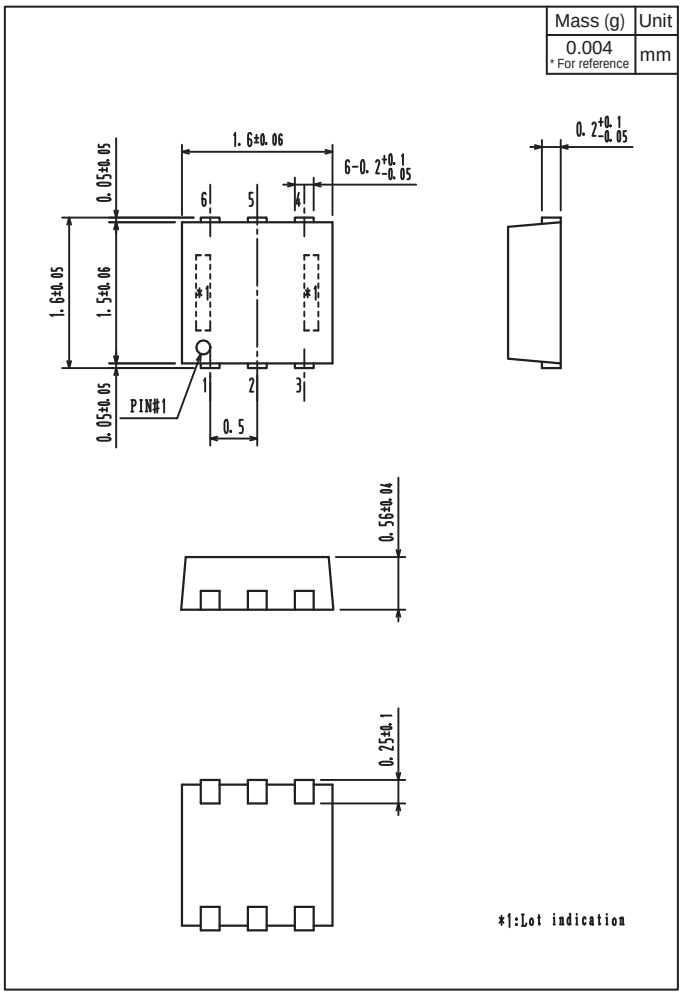

VGS – Qg
VDS=10V
ID=1.8A
Gate to Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT13115


A S O
IDP=7.2A (PW≤10μs)
ID=1.8A
100μs
1ms
10ms
100ms
DC operation (Ta=25°C)
Operation in this area is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate (900mm2×0.8mm)
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT15990

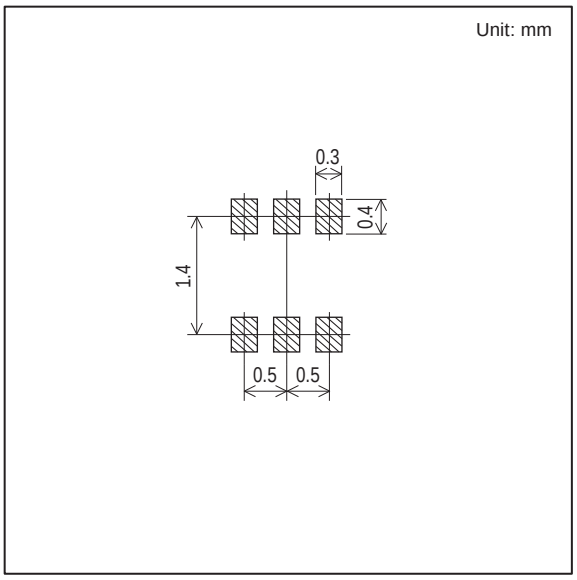

PD – Ta
When mounted on ceramic substrate
(900mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT15991

Outline Drawing

SCH1436-TL-H



Land Pattern Example



Note on usage : Since the SCH1436 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.